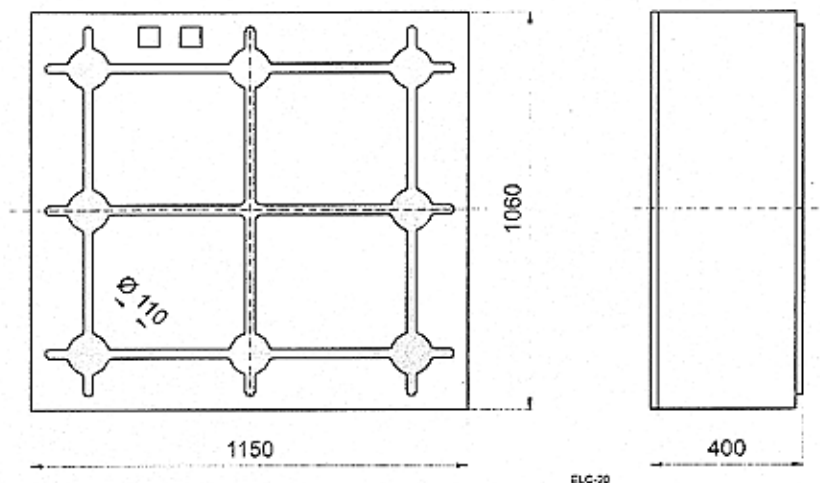


Radiation	Type	Technology	Electrodes
Infrared	ELC-900-29-2	AlGaAs/GaAs DH	N (cathode) up

Outline (dimensions in microns)**Optical and Electrical Characteristics**

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.35	1.7	V
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1.45	1.8	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	5			V
Radiant power	$I_F = 20 \text{ mA}$	Φ_e	2.8	3.2		mW
Radiant power	$I_F = 50 \text{ mA}$	Φ_e	7	8		mW
Peak wavelength	$I_F = 50 \text{ mA}$	λ_p		900		nm
Spectral bandwidth at 50%	$I_F = 50 \text{ mA}$	$\Delta\lambda_{0.5}$		75	80	nm
Switching time	$I_F = 50 \text{ mA}$	t_r, t_f		400		ns

Labeling

Type	Lot N°	Φ_e (typ, min, max)	Quantity
ELC-900-29-2			

Packing

Chips on adhesive film with wire-bond side on top